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# FOR USE BY ELECTRICIANS OVERSEAS :

**最新トランジスタ規格表** (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T <sub>b</sub> =25°C)					電気的特性 (T <sub>b</sub> =25°C)										外形	備考
				V <sub>ceo</sub> (V)	V <sub>ceo</sub> (V)	I <sub>c</sub> (mA)	P <sub>c</sub> (mW)	T <sub>j</sub> (°C)	I <sub>ceo</sub> 最大値 (μA)	直流又はパルスI <sub>BE</sub>		バイアス		h <sub>FE</sub>	h <sub>ie</sub> h <sub>ie</sub> * (Ω)	h <sub>re</sub> h <sub>re</sub> * (×10 <sup>-4</sup> )	h <sub>oe</sub> h <sub>oe</sub> * (μS)	f <sub>αb</sub> f <sub>r</sub> * (Mc)		
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I<sub>CBO</sub> MAXIMUM VALUE AND V<sub>CB</sub> VALUE (CRITERIA FOR MEASURING I<sub>CBO</sub>)
- 7 STANDARD VALUE OF DC/PULSE h<sub>FE</sub> AND V<sub>CE</sub>, I<sub>C</sub> (CRITERIA FOR MEASURING DC/PULSE h<sub>FE</sub>)
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V<sub>CB</sub>, I<sub>E</sub> (CRITERIA FOR MEASURING h PARAMETERS)

- \* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 f<sub>αb</sub> OF RF CHARACTERISTIC, EXCEPT IN CASE OF \* WHICH INDICATES VALUE OF f<sub>r</sub>.
- 10 C<sub>ob</sub> AND r<sub>bb'</sub> OF RF CHARACTERISTICS EXCEPT IN CASE OF \* IN r<sub>bb'</sub> COLUMN WHICH INDICATES VALUE OF h<sub>ie</sub> (real)
- 11 OUTLINE
- 12 REMARKS

:とコンプリ: COMPLEMENTARY TO .....

型名	社名	用途	構造	最大定格 (T <sub>a</sub> = 25°C)						電 気 的 特 性 (T <sub>a</sub> = 25°C)										外 形	備 考				
				V <sub>CB0</sub> (V)	V <sub>EB0</sub> (V)	I <sub>C</sub> (mA)	P <sub>C</sub> (mW)	T <sub>J</sub> (°C)	I <sub>CB0</sub> 最大値 (μA)	V <sub>CE</sub> (V)	直流又はパルス V <sub>CE</sub> (V)	h <sub>FE</sub> I <sub>C</sub> (mA)	バイアス V <sub>CB</sub> (V)	I <sub>E</sub> (mA)	h <sub>FE</sub> h <sub>FB</sub> *	h <sub>ie</sub> h <sub>ib</sub> * (Ω)	h <sub>re</sub> h <sub>ry</sub> * (×10 <sup>-4</sup> )	h <sub>oe</sub> h <sub>ob</sub> * (μΩ)	f <sub>βB</sub> f <sub>T</sub> * (Mc)			C <sub>ob</sub> (pF)	r <sub>bb</sub> h <sub>ie(real)</sub> * (Ω)		
2SC2202																									
"	2203																								
"	2204	東芝	SW	Si.TMe	800	5	30A	250W (T <sub>c</sub> =25°C)	150	1mA	800	>10	5	30A											
"	2205																								
"	2206	松下	RF	Si.EP	30	5	30	400	135	0.1	10	100	10	1	10	-1									
"	2207	日立	PA	Si.E	80	4	8A	25W (T <sub>c</sub> =25°C)	150	100	60	30-150	10	2A											
"	2208	"	SW	Si.EPa	120	7	5A	800	175	100	120	>1000	5	5A											
"	2209	松下	PA	Si.EP	50	5	1.5A	10W (T <sub>c</sub> =25°C)	150	1	20	120	5	1A	5	-500									
"	2210	三洋	RF.Conv	"	30	5	30	250	125	0.1	10	40-320	6	1	6	-1									
"	2211																								
"	2212	ソニー	RF	Si.E	15	3	20	250	100	I <sub>CES</sub> 0.2	10	30-170	10	3											
"	2213	"	Osc.	Si.EPa	30	4	50	250	100	I <sub>CES</sub> 0.2	15	70	10	5											
"	2214	"	PA.SW	"	100	6	4A	10W (T <sub>c</sub> =25°C)	175	0.5	50	100	2	100											
"	2215	東芝	RF	Si.P	40	4	50	250	125	0.1	40	>30	10	4	10	-4									
"	2216	"	"	Si.EP	50	4	50	300	125	0.1	50	40-140	12.5	12.5	12.5	-12.5									
"	2217	日電	RF.LN	Si.E	20	1.5	80	580	200	1	8	100	8	20	8	-20									
"	2218	"	"	"	20	1.5	80	350	200	1	8	100	8	20	8	-20									
"	2219	"	"	"	20	1.5	80	700 (T <sub>c</sub> =10°C)	200	1	8	100	8	20	8	-20									
"	2220	東芝	SW	Si.TMe	500	5	30A	250W (T <sub>c</sub> =25°C)	150	1mA	500	>10	5	30A											
"	2221	日電	RF.PA	Si.E	25	2.5	750	7.5W (T <sub>c</sub> =25°C)	175	250	20	60	7	200											
"	2222	"	"	"	25	2.5	1.5A	17W (T <sub>c</sub> =25°C)	175	500	20	60	7	400											
"	2223	"	RF.LN	"	30	4	20	150	125	0.1	25	90	6	1	6	-1									
"	2224	"	PA	Si.EP	200	5	200	10W (T <sub>c</sub> =25°C)	150	1	180	180	10	10	10	-10									
"	2225																								
"	2226																								
"	2227																								
"	2228	三洋	RF	Si.TP	160	5	50	750	125	1	160	40-320	10	10	30	-10									
"	2229	東芝	AF.PA.SW	Si.T	200	5	50	800	150	0.1	200	70-240	5	10	30	-10									
"	2230	"	AF.RF	"	200	5	100	800	150	0.1	200	120-400	10	10	10	-10									
"	2231	"	"	"	200	5	200	1.5W	150	0.1	200	100-320	10	50	10	-50									

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